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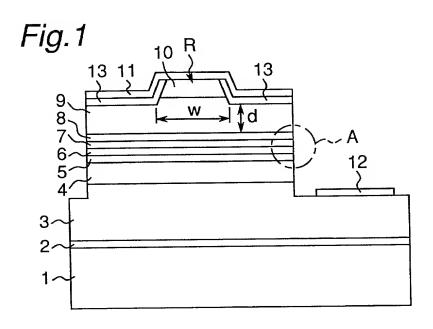
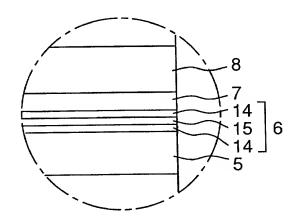


Fig.2



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Fig.3

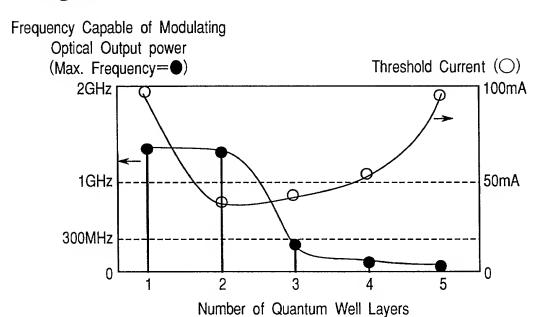
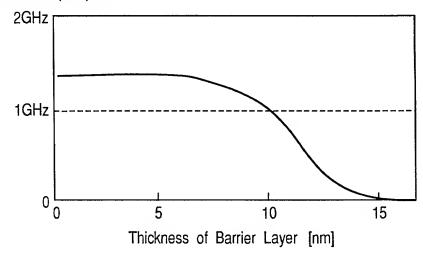


Fig.4

Frequency Capable of Modulating
Optical Output power



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Fig.5

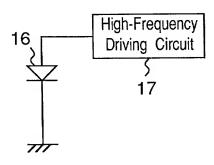


Fig.6

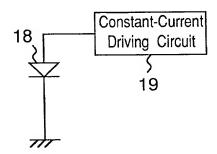
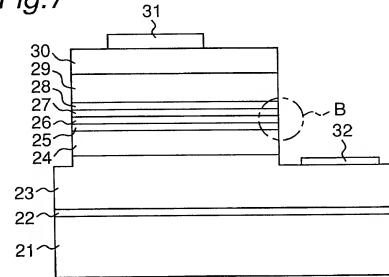


Fig.7



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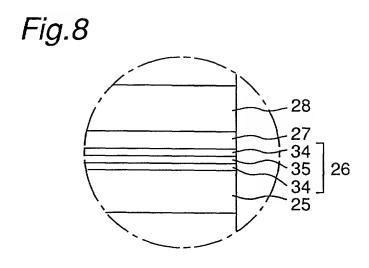
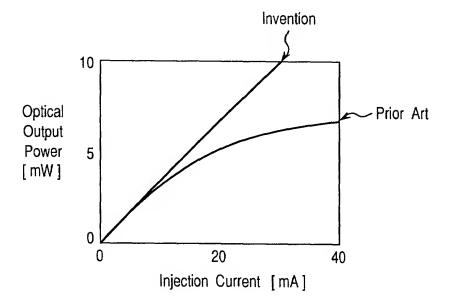


Fig.9



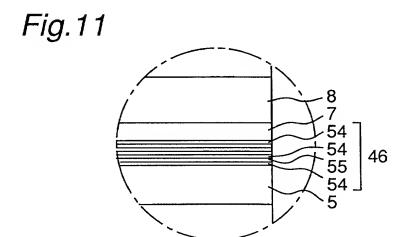
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Fig.10 10 13 11 13 8 46-12 5 3-



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Fig.12

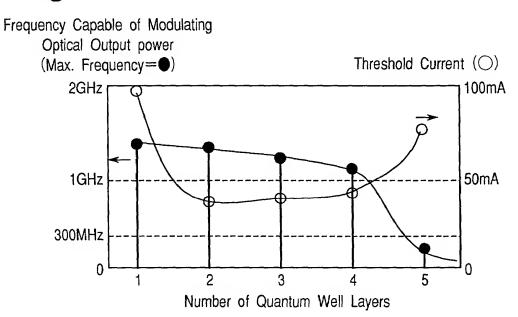
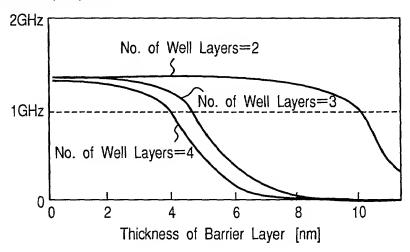


Fig.13

Frequency Capable of Modulating
Optical Output power



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Fig.14

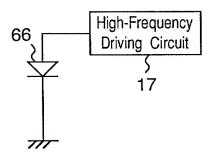


Fig.15

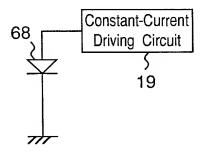
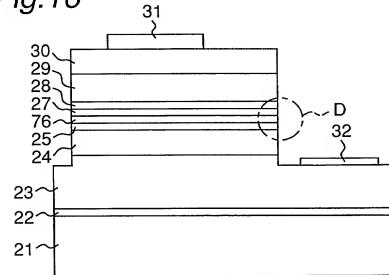


Fig. 16



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Fig.17

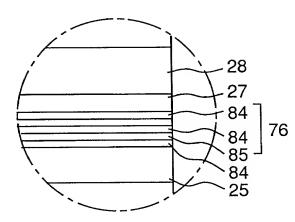
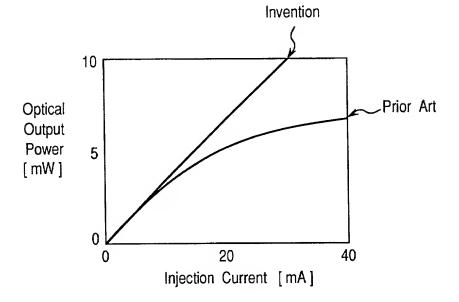


Fig.18



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Fig.19

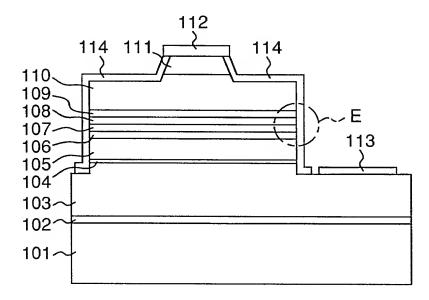
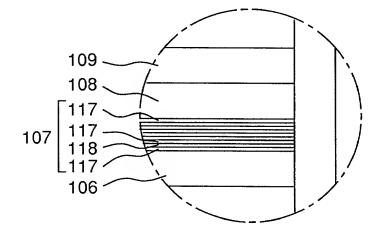


Fig.20



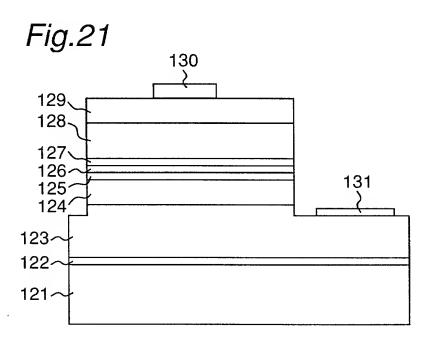
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